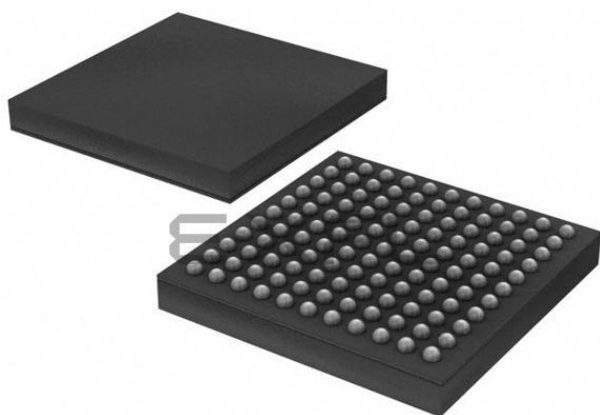




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

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Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	93
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	120-VFBGA
Supplier Device Package	120-BGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg395f1024g-e-bga120r

2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32GG microcontroller. The flash memory is readable and writable from both the Cortex-M3 and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

2.1.4 Direct Memory Access Controller (DMA)

The Direct Memory Access (DMA) controller performs memory operations independently of the CPU. This has the benefit of reducing the energy consumption and the workload of the CPU, and enables the system to stay in low energy modes when moving for instance data from the USART to RAM or from the External Bus Interface to a PWM-generating timer. The DMA controller uses the PL230 μ DMA controller licensed from ARM.

2.1.5 Reset Management Unit (RMU)

The RMU is responsible for handling the reset functionality of the EFM32GG.

2.1.6 Energy Management Unit (EMU)

The Energy Management Unit (EMU) manage all the low energy modes (EM) in EFM32GG microcontrollers. Each energy mode manages if the CPU and the various peripherals are available. The EMU can also be used to turn off the power to unused SRAM blocks.

2.1.7 Clock Management Unit (CMU)

The Clock Management Unit (CMU) is responsible for controlling the oscillators and clocks on-board the EFM32GG. The CMU provides the capability to turn on and off the clock on an individual basis to all peripheral modules in addition to enable/disable and configure the available oscillators. The high degree of flexibility enables software to minimize energy consumption in any specific application by not wasting power on peripherals and oscillators that are inactive.

2.1.8 Watchdog (WDOG)

The purpose of the watchdog timer is to generate a reset in case of a system failure, to increase application reliability. The failure may e.g. be caused by an external event, such as an ESD pulse, or by a software failure.

2.1.9 Peripheral Reflex System (PRS)

The Peripheral Reflex System (PRS) system is a network which lets the different peripheral module communicate directly with each other without involving the CPU. Peripheral modules which send out Reflex signals are called producers. The PRS routes these reflex signals to consumer peripherals which apply actions depending on the data received. The format for the Reflex signals is not given, but edge triggers and other functionality can be applied by the PRS.

2.1.10 External Bus Interface (EBI)

The External Bus Interface provides access to external parallel interface devices such as SRAM, FLASH, ADCs and LCDs. The interface is memory mapped into the address bus of the Cortex-M3. This enables seamless access from software without manually manipulating the IO settings each time a read or write is performed. The data and address lines are multiplexed in order to reduce the number of pins required

2.1.26 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has two single ended output buffers which can be combined into one differential output. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.27 Operational Amplifier (OPAMP)

The EFM32GG395 features 3 Operational Amplifiers. The Operational Amplifier is a versatile general purpose amplifier with rail-to-rail differential input and rail-to-rail single ended output. The input can be set to pin, DAC or OPAMP, whereas the output can be pin, OPAMP or ADC. The current is programmable and the OPAMP has various internal configurations such as unity gain, programmable gain using internal resistors etc.

2.1.28 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSE[™]), is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.29 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32GG395 to keep track of time and retain data, even if the main power source should drain out.

2.1.30 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.31 General Purpose Input/Output (GPIO)

In the EFM32GG395, there are 93 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32GG395 is a subset of the feature set described in the EFM32GG Reference Manual. Table 2.1 (p. 8) describes device specific implementation of the features.

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}\text{C}$ and $V_{DD}=3.0\text{ V}$, as defined in Table 3.2 (p. 10), unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10).

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150	$^{\circ}\text{C}$
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	$^{\circ}\text{C}$
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		$V_{DD}+0.3$	V
I_{IOMAX}	Current per I/O pin (sink)				100	mA
	Current per I/O pin (source)				-100	mA

3.3 General Operating Conditions

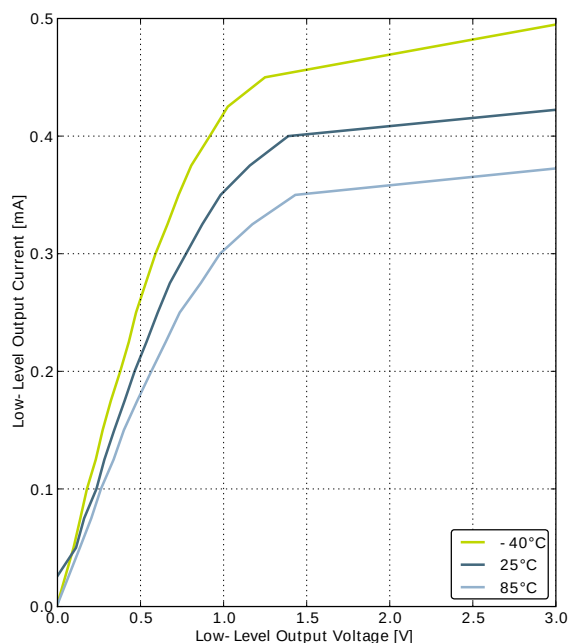
3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

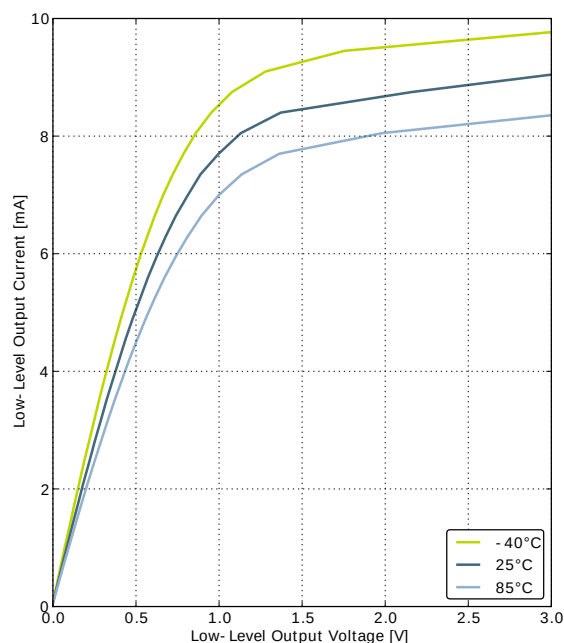
Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	$^{\circ}\text{C}$
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		Sourcing 20 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.60V_{DD}$			V
		Sourcing 20 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.80V_{DD}$			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.20V_{DD}$		V
		Sinking 0.1 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.10V_{DD}$		V
		Sinking 1 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.10V_{DD}$		V
		Sinking 1 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.05V_{DD}$		V
		Sinking 6 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.30V_{DD}$	V
		Sinking 6 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.20V_{DD}$	V
		Sinking 20 mA, $V_{DD}=1.98$ V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.35V_{DD}$	V
		Sinking 20 mA, $V_{DD}=3.0$ V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.20V_{DD}$	V
I_{IOLEAK}	Input leakage current	High Impedance IO connected to GROUND or V_{DD}		± 0.1	± 40	nA
R_{PU}	I/O pin pull-up resistor			40		kOhm
R_{PD}	I/O pin pull-down resistor			40		kOhm
R_{IOESD}	Internal ESD series resistor			200		Ohm
$t_{IOGLITCH}$	Pulse width of pulses to be removed by the glitch suppression filter		10		50	ns
t_{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capacitance $C_L=12.5-25$ pF.	$20+0.1C_L$		250	ns
		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance $C_L=350-600$ pF	$20+0.1C_L$		250	ns
V_{IOHYST}	I/O pin hysteresis ($V_{IOTHR+} - V_{IOTHR-}$)	$V_{DD} = 1.98 - 3.8$ V	$0.10V_{DD}$			V

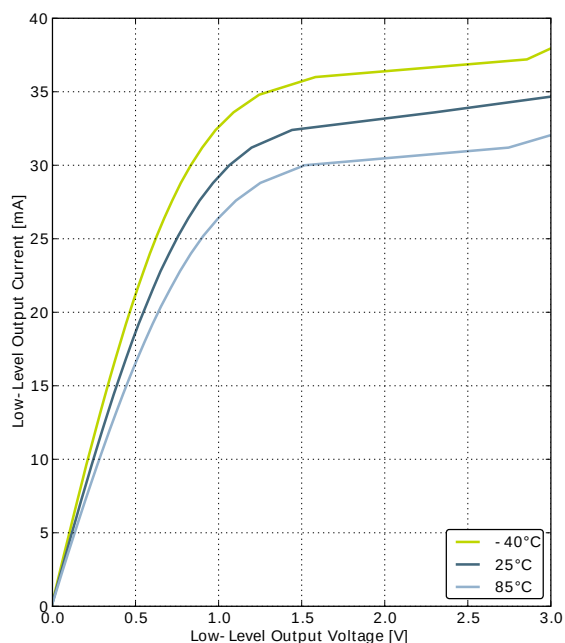
Figure 3.6. Typical Low-Level Output Current, 3V Supply Voltage



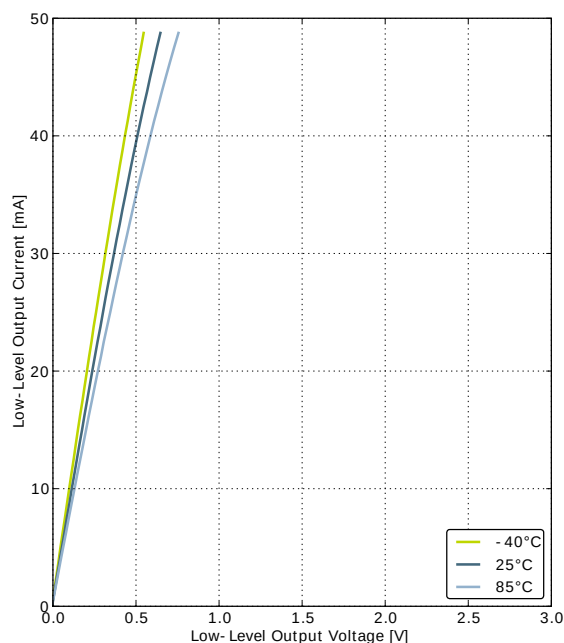
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

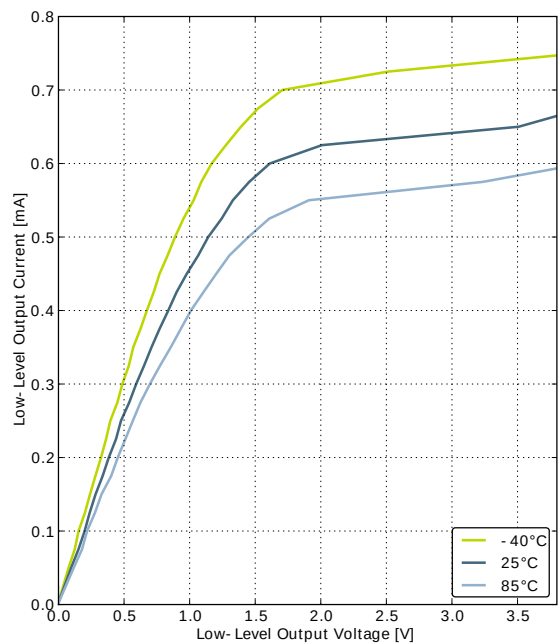


GPIO_Px_CTRL DRIVEMODE = STANDARD

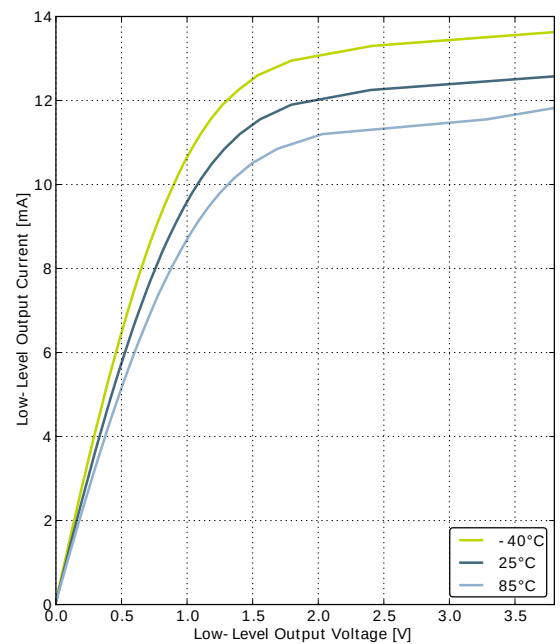


GPIO_Px_CTRL DRIVEMODE = HIGH

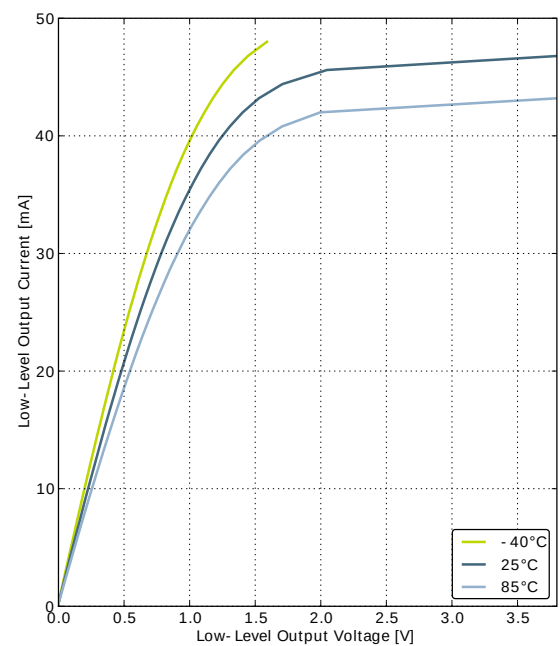
Figure 3.8. Typical Low-Level Output Current, 3.8V Supply Voltage



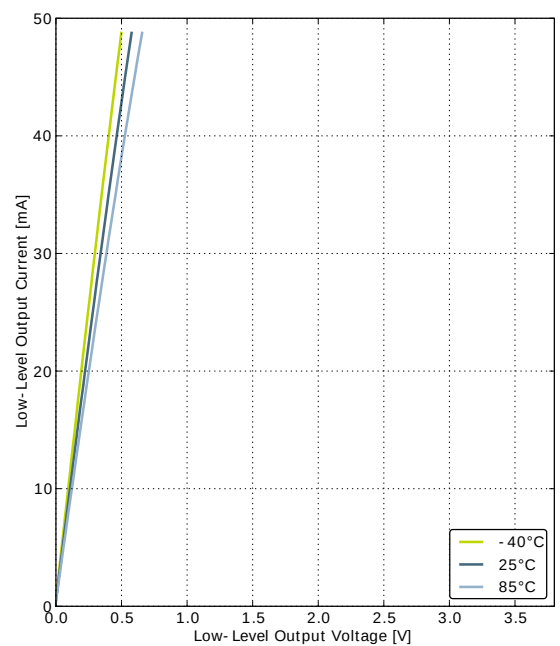
GPIO_Px_CTRL DRIVEMODE = LOWEST



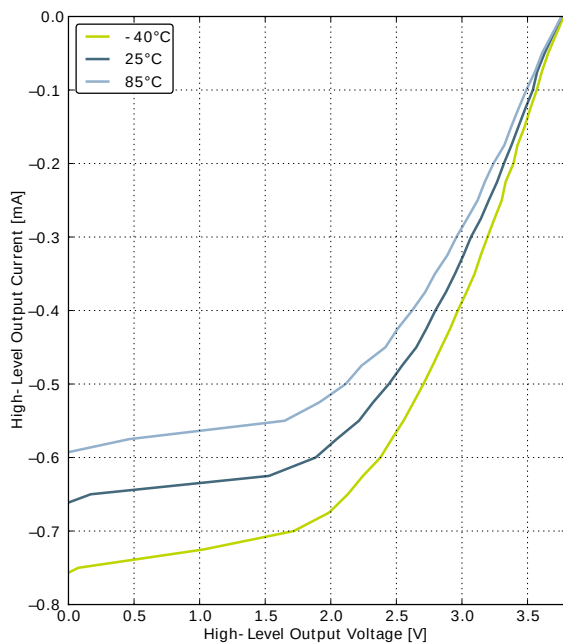
GPIO_Px_CTRL DRIVEMODE = LOW



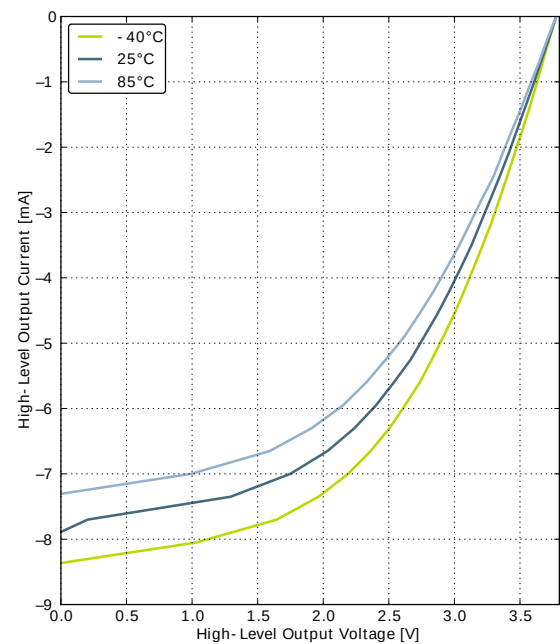
GPIO_Px_CTRL DRIVEMODE = STANDARD



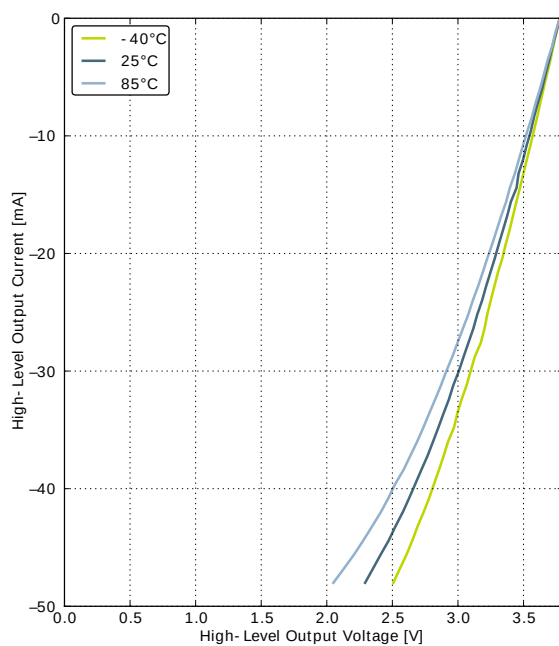
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.9. Typical High-Level Output Current, 3.8V Supply Voltage

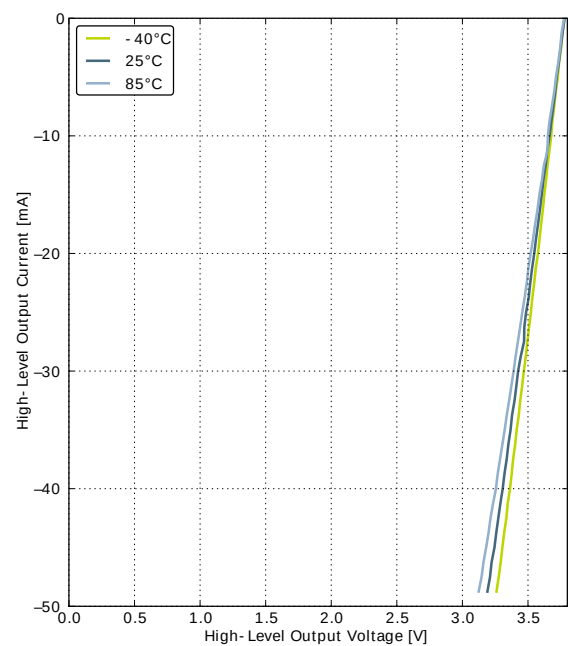
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD

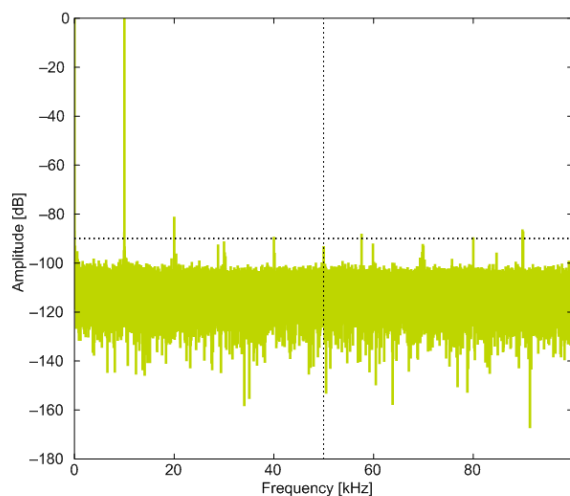


GPIO_Px_CTRL DRIVEMODE = HIGH

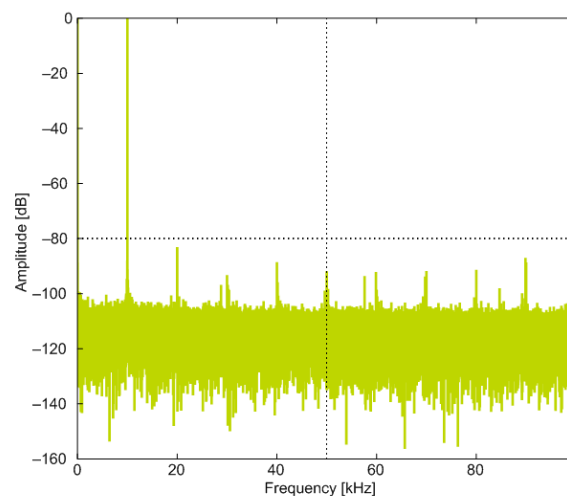
Symbol	Parameter	Condition	Min	Typ	Max	Unit
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MOhm
R _{ADCFLT}	Input RC filter resistance			10		kOhm
C _{ADCFLT}	Input RC filter/de-coupling capacitance			250		fF
f _{ADCCLK}	ADC Clock Frequency				13	MHz
t _{ADCCONV}	Conversion time	6 bit	7			ADC-CLK Cycles
		8 bit	11			ADC-CLK Cycles
		12 bit	13			ADC-CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC-CLK Cycles
t _{ADCACQVDD3}	Required acquisition time for VDD/3 reference		2			μs
t _{ADCSTART}	Startup time of reference generator and ADC core in NORMAL mode			5		μs
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		μs
SNR _{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V _{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, 2xV _{DD} reference		69		dB

3.10.1 Typical performance

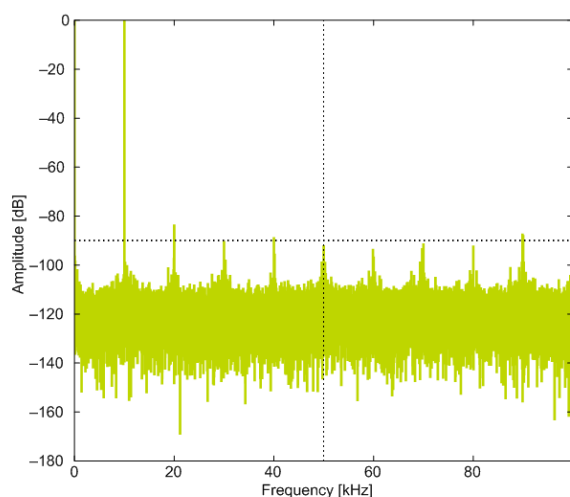
Figure 3.19. ADC Frequency Spectrum, $V_{dd} = 3V$, Temp = 25°C



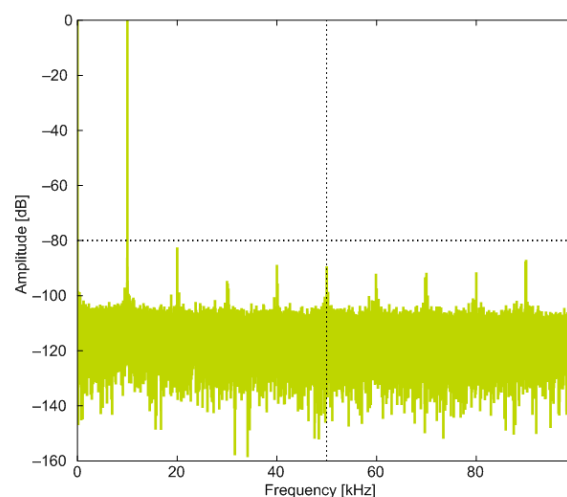
1.25V Reference



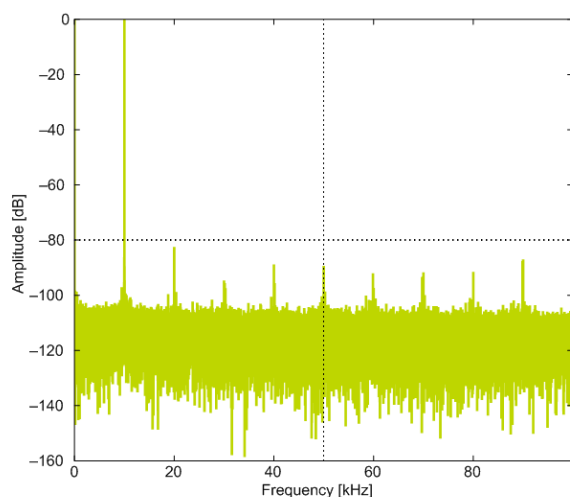
2.5V Reference



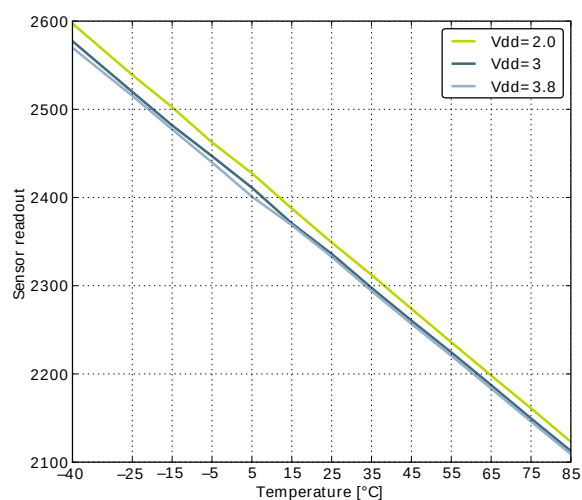
2XVDDVSS Reference



5VDIFF Reference



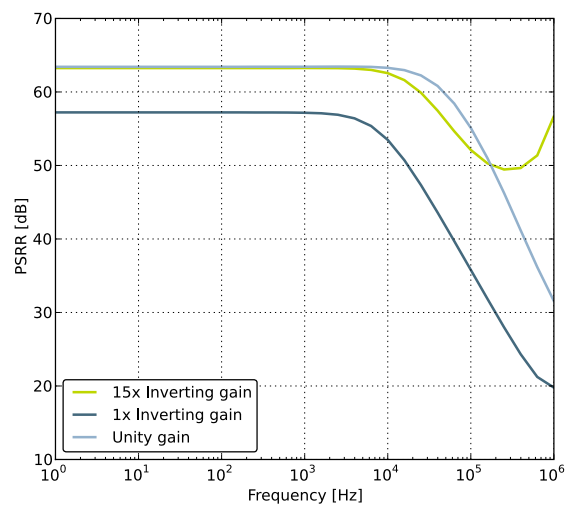
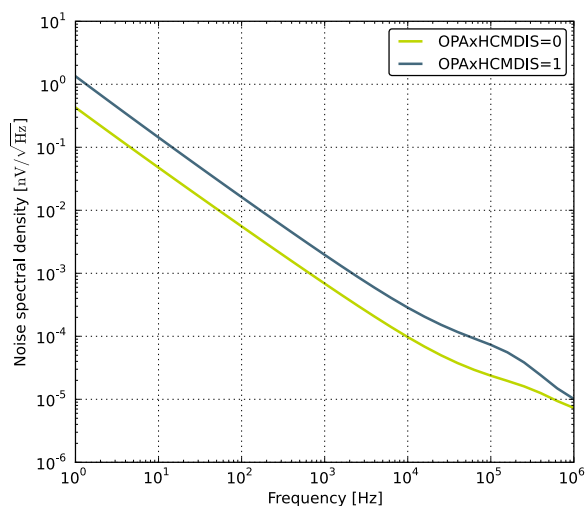
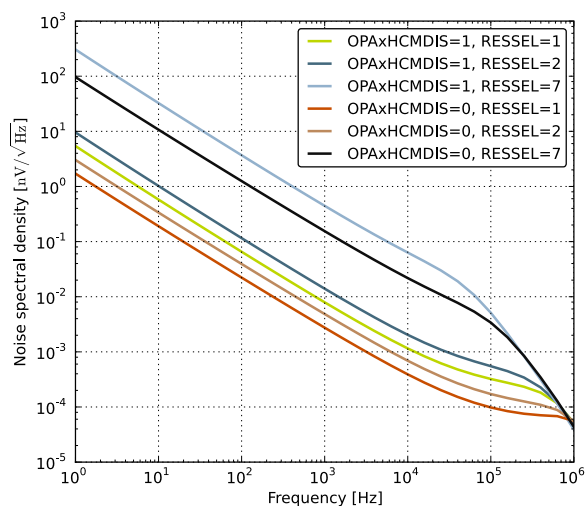
VDD Reference

Figure 3.24. ADC Temperature sensor readout

3.11 Digital Analog Converter (DAC)

Table 3.15. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V _{DD}	V
		VDD voltage reference, differential	-V _{DD}		V _{DD}	V
V _{DACCM}	Output common mode voltage range		0		V _{DD}	V
I _{DAC}	Active current including references for 2 channels	500 kSamples/s, 12 bit		400 ¹	600 ¹	μA
		100 kSamples/s, 12 bit		200 ¹	260 ¹	μA
		1 kSamples/s 12 bit NORMAL		17 ¹	25 ¹	μA
SR _{DAC}	Sample rate				500	ksamples/s
f _{DAC}	DAC clock frequency	Continuous Mode			1000	kHz
		Sample/Hold Mode			250	kHz
		Sample/Off Mode			250	kHz
CYC _{DACCONV}	Clock cycles per conversion			2		
t _{DACCONV}	Conversion time		2			μs
t _{DACSETTLE}	Settling time			5		μs
SNR _{DAC}	Signal to Noise Ratio (SNR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		58		dB

Figure 3.27. OPAMP Negative Power Supply Rejection Ratio**Figure 3.28. OPAMP Voltage Noise Spectral Density (Unity Gain) $V_{out}=1V$** **Figure 3.29. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)**

3.13 Analog Comparator (ACMP)

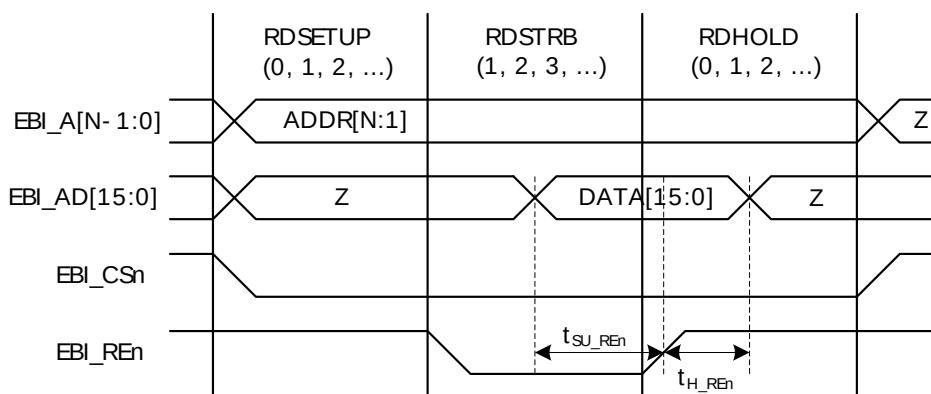
Table 3.17. ACMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULL-BIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.6	μA
		BIASPROG=0b1111, FULL-BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	12	μA
		BIASPROG=0b1111, FULL-BIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		250	520	μA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		μA
		Internal voltage reference		5		μA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULL-BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		43		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		78		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		111		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		145		kOhm
$t_{ACMPSTART}$	Startup time				10	μs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 43) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current

$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \quad (3.1)$$

Figure 3.34. EBI Read Enable Related Timing Requirements**Table 3.22. EBI Read Enable Related Timing Requirements**

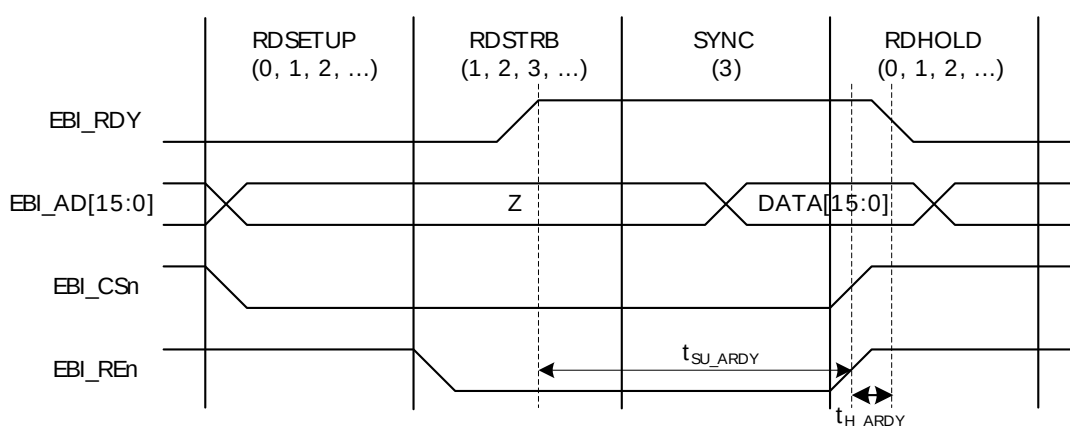
Symbol	Parameter	Min	Typ	Max	Unit
$t_{SU_REn}^{1\ 2\ 3\ 4}$	Setup time, from EBI_AD valid to trailing EBI_REn edge		37		ns
$t_{H_Ren}^{1\ 2\ 3\ 4}$	Hold time, from trailing EBI_REn edge to EBI_AD invalid		-1		ns

¹Applies for all addressing modes (figure only shows D16A8).

²Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)

³Applies for all polarities (figure only shows active low signals)

⁴Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Figure 3.35. EBI Ready/Wait Related Timing Requirements**Table 3.23. EBI Ready/Wait Related Timing Requirements**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{SU_ARDY}^{1\ 2\ 3\ 4}$	Setup time, from EBI_ARDY valid to trailing EBI_REn, EBI_WEn edge	$37 + (3 * t_{HFCORECLK})$			ns

BGA120 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
A4	PE9		EBI_AD01 #0/1/2	PCNT2_S1IN #1		
A5	PD11		EBI_CS2 #0/1/2			
A6	PD9		EBI_CS0 #0/1/2			
A7	PF7		EBI_BL1 #0/1/2	TIM0_CC1 #2	U0_RX #0	
A8	PF5		EBI_REn #0/2	TIM0_CDTI2 #2/5	USB_VBUSEN #0	PRS_CH2 #1
A9	PF4		EBI_WEn #0/2	TIM0_CDTI1 #2/5		PRS_CH1 #1
A10	PF2		EBI_ARDY #0/1/2	TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0 DBG_SWO #0 GPIO_EM4WU4
A11	USB_VREGI					
A12	USB_VREGO					
A13	PF11				U1_RX #1 USB_DP	
B1	PA15		EBI_AD08 #0/1/2	TIM3_CC2 #0		
B2	PE13		EBI_AD05 #0/1/2		US0_TX #3 US0_CS #0 I2C0_SCL #6	LES_ALTEX7 #0 ACMP0_O #0 GPIO_EM4WU5
B3	PE11		EBI_AD03 #0/1/2	TIM1_CC1 #1	US0_RX #0	LES_ALTEX5 #0 BOOT_RX
B4	PE8		EBI_AD00 #0/1/2	PCNT2_S0IN #1		PRS_CH3 #1
B5	PD12		EBI_CS3 #0/1/2			
B6	PD10		EBI_CS1 #0/1/2			
B7	PF8		EBI_WEn #1	TIM0_CC2 #2		ETM_TCLK #1
B8	PF6		EBI_BL0 #0/1/2	TIM0_CC0 #2	U0_TX #0	
B9	PF3		EBI_ALE #0	TIM0_CDTI0 #2/5		PRS_CH0 #1 ETM_TD3 #1
B10	PF1			TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 I2C0_SCL #5 LEU0_RX #3	DBG_SWDIO #0/1/2/3 GPIO_EM4WU3
B11	PF12				USB_ID	
B12	USB_VBUS	USB 5.0 V VBUS input.				
B13	PF10				U1_TX #1 USB_DM	
C1	PA1		EBI_AD10 #0/1/2	TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0
C2	PA0		EBI_AD09 #0/1/2	TIM0_CC0 #0/1/4	I2C0_SDA #0 LEU0_RX #4	PRS_CH0 #0 GPIO_EM4WU0
C3	PE10		EBI_AD02 #0/1/2	TIM1_CC0 #1	US0_TX #0	BOOT_TX
C4	PD13					ETM_TD1 #1
C5	VSS	Ground.				
C6	IOVDD_0	Digital IO power supply 0.				
C7	PF9		EBI_REn #1			ETM_TD0 #1
C8	VSS	Ground.				
C9	IOVDD_1	Digital IO power supply 1.				
C10	PF0			TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 I2C0_SDA #5	DBG_SWCLK #0/1/2/3

Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	PA15	PA14	PA13	PA12	PA11	PA10	PA9	PA8	PA7	PA6	PA5	PA4	PA3	PA2	PA1	PA0
Port B	PB15	PB14	PB13	PB12	PB11	PB10	PB9	PB8	PB7	PB6	PB5	PB4	PB3	PB2	PB1	PB0
Port C	PC15	PC14	PC13	PC12	PC11	PC10	PC9	PC8	PC7	PC6	PC5	PC4	PC3	PC2	PC1	PC0
Port D	PD15	PD14	PD13	PD12	PD11	PD10	PD9	PD8	PD7	PD6	PD5	PD4	PD3	PD2	PD1	PD0
Port E	PE15	PE14	PE13	PE12	PE11	PE10	PE9	PE8	PE7	PE6	PE5	PE4	PE3	PE2	PE1	PE0
Port F	-	-	-	PF12	PF11	PF10	PF9	PF8	PF7	PF6	PF5	PF4	PF3	PF2	PF1	PF0

4.4 Opamp Pinout Overview

The specific opamp terminals available in *EFM32GG395* is shown in Figure 4.2 (p. 64) .

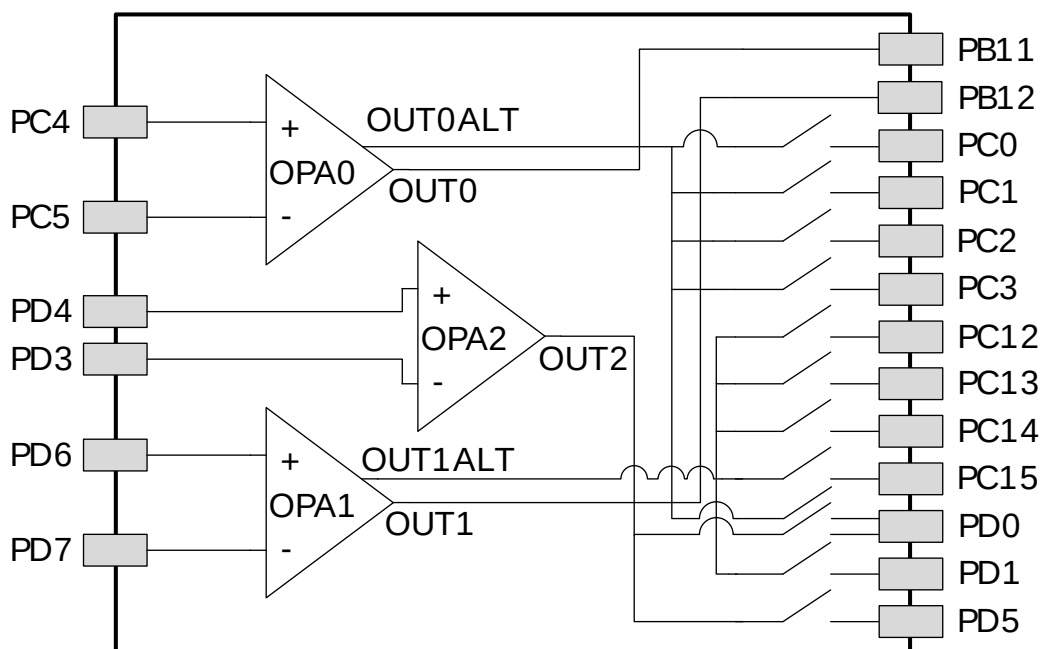
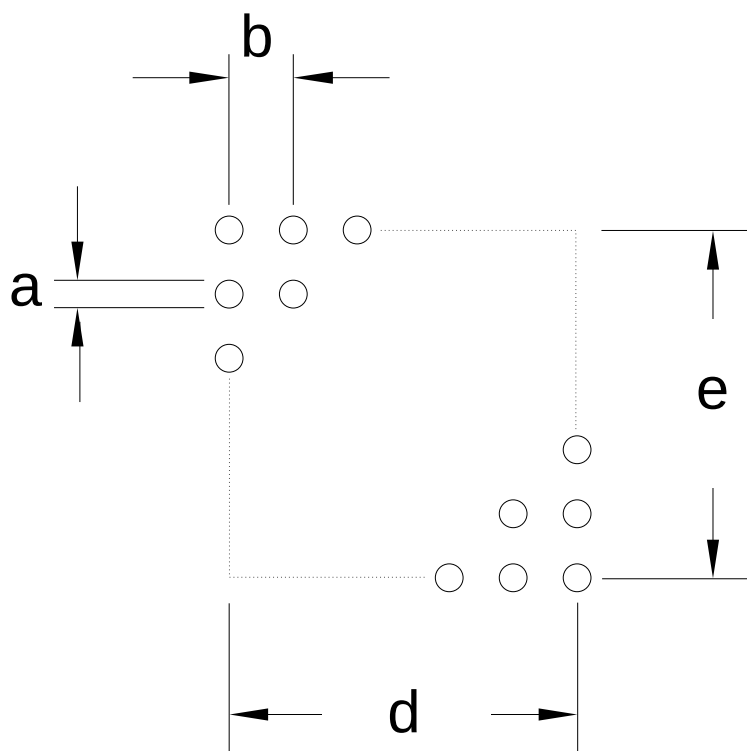
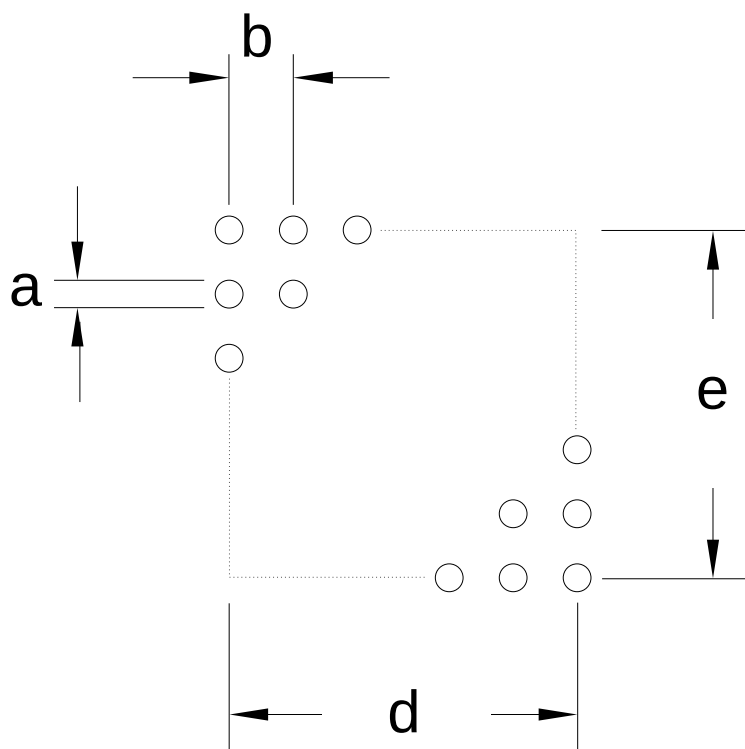
Figure 4.2. Opamp Pinout

Figure 5.2. BGA120 PCB Solder Mask**Table 5.2. BGA120 PCB Solder Mask Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)
a	0.35
b	0.50
d	6.00
e	6.00

Figure 5.3. BGA120 PCB Stencil Design**Table 5.3. BGA120 PCB Stencil Design Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)
a	0.25
b	0.50
d	6.00
e	6.00

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 65) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

7.5 Revision 1.10

June 28th, 2013

Updated PCB Land Pattern, PCB Solder Mask and PCB Stencil Design figures.

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 0.98

May 25th, 2012

Corrected BGA solder balls material description.

Corrected EM3 current consumption in the Electrical Characteristics section.

7.8 Revision 0.96

February 28th, 2012

Added reference to errata document.

Corrected BGA120 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.9 Revision 0.95

September 28th, 2011

Flash configuration for Giant Gecko is now 1024KB or 512KB. For flash sizes below 512KB, see the Leopard Gecko Family.

Corrected operating voltage from 1.8 V to 1.85 V.

Added rising POR level to Electrical Characteristics section.

Updated Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup.

Added Gain error drift and Offset error drift to ADC table.

Added Opamp pinout overview.

Added reference to errata document.

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